

ABSTRACT OF THE DISCLOSURE

A process for introducing structures that have different dimensions, particularly with regard to depth, in which just one lithography level is required, is disclosed. This is achieved by use of a layer stack deposited on a substrate, where one layer in particular is used to store information related to the dimensioning of the different structures. The layer is partially opened up to expose the substrate at locations corresponding to where deep structures are to be formed. Deep structures are subsequently etched into the substrate, after which the layer is opened up at locations corresponding to where shallow structures are to be formed. The latter locations are subsequently etched to the desired depth of the shallower structures. The process can be used instead of conventional the dual damascene technology for the structuring of contact holes and interconnects.

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